

In the Claims

Please amend the claims as indicated below.

~~38.~~ 38. (Amended) A method of forming a capacitor including:

~~forming a first electrode selected from a group consisting of transition metals, conductive metal-oxides, alloys thereof, and combinations thereof;~~

~~forming a dielectric on the first electrode and an uppermost surface of a substrate assembly; and~~

~~forming a second electrode on the dielectric and the uppermost surface of the substrate assembly.~~

~~49.~~ 49. (Amended) The method of claim 38, further comprising forming the substrate assembly before forming the first electrode.

~~51.~~ 51. (Twice Amended) The method of claim 38, wherein forming the first electrode includes:

~~forming a layer of hemispherical grain on the substrate assembly; and~~

~~forming the first electrode on the hemispherical grain polysilicon.~~

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*52*

52. (Amended) A method of forming a capacitor, comprising:

forming a layer of hemispherical grain polysilicon;

forming a first electrode on the hemispherical grain polysilicon, wherein the first electrode is selected from a group consisting of transition metals, conductive metal-oxides, alloys thereof, and combinations thereof;

forming a dielectric on the first electrode and an uppermost surface of a substrate assembly; and

forming a second electrode on the dielectric and the uppermost surface of the substrate assembly.

*Subst*

57. (Amended) The method of claim 52, further comprising forming the substrate assembly before forming the first electrode.

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*DU*

58. (Amended) A method, comprising:

forming a substrate assembly;

forming a layer of hemispherical grain polysilicon on the substrate assembly;

forming a first electrode on the hemispherical grain polysilicon, wherein the first electrode is selected from a group consisting of transition metals, conductive metal-oxides, alloys thereof, and combinations thereof;

removing a portion of the substrate assembly;

removing the hemispherical grain polysilicon;